

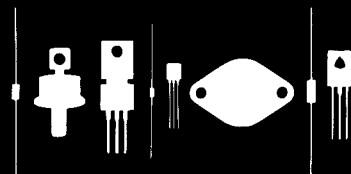
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145 Adams Avenue
Hauppauge, New York 11788



2N2726

2N2727

NPN SILICON TRANSISTOR

JEDEC TO-39 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N2726, 2N2727 types are Silicon NPN Transistors designed for general purpose amplifier applications.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

	<u>SYMBOL</u>		<u>UNIT</u>
Collector-Base Voltage	V_{CB0}	200	V
Collector-Emitter Voltage*	V_{CER}	200	V
Collector-Emitter Voltage	V_{CEO}	150	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	500	mA
Base Current	I_B	250	mA
Power Dissipation	P_D	1.0	W
Power Dissipation ($T_C=25^{\circ}\text{C}$)	P_D	5.0	W
Operating & Storage Junction Temperature	T_J, T_{stg}	-65 TO +200	$^{\circ}\text{C}$

* $R_{BE}=5\text{K}\Omega$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>2N2726</u>		<u>2N2727</u>		<u>UNIT</u>
		<u>MIN</u>	<u>MAX</u>	<u>MIN</u>	<u>MAX</u>	
I_{CB0}	$V_{CB}=100\text{V}$		1.0		1.0	μA
I_{CB0}	$V_{CB}=100\text{V}, T_A=150^{\circ}\text{C}$		100		100	μA
I_{CEV}	$V_{CE}=200\text{V}, V_{BE}=1.5\text{V}$		300		300	μA
I_{CEV}	$V_{CE}=100\text{V}, V_{BE}=1.5\text{V}, T_A=150^{\circ}\text{C}$		150		150	μA
I_{CEO}	$V_{CE}=100\text{V}$		250		250	μA
I_{EBO}	$V_{EB}=6.0\text{V}$		250		250	μA
BV_{CER}	$I_C=50\text{mA}, R_{BE}\leq 5\text{K}\Omega$	200		200		V
BV_{CEO}	$I_C=20\text{mA}$	150		150		V
$V_{CE(SAT)}$	$I_C=200\text{mA}, I_B=40\text{mA}$		2.0		2.0	V
$V_{BE(ON)}$	$V_{CE}=10\text{V}, I_C=200\text{mA}$		3.0		3.0	V
h_{FE}	$V_{CE}=10\text{V}, I_C=200\text{mA}$	30	90	75	150	
h_{FE}	$V_{CE}=10\text{V}, I_C=200\text{mA}, T_A=55^{\circ}\text{C}$	15		30		
h_{fe}	$V_{CE}=30\text{V}, I_C=30\text{mA}, f=1.0\text{kHz}$	30		75		
f_T	$V_{CE}=30\text{V}, I_C=30\text{mA}, f=1.0\text{MHz}$	5		10		MHz

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